Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-32 (canceled)

Claim 33 (original): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal layer comprising an approximately hexagonal prismoid, having a face oriented about an S- plane, and a top region oriented about a C-plane; and

a layer of a first conductivity type, an active layer, and a layer of a second conductivity type each formed along at least a portion of the approximately hexagonal prismoid.

Claims 34-82 (canceled)

Claim 83 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a surface plane;

a crystal layer including a crystal surface oriented along a crystal surface plane diagonally intersecting the substrate surface plane; and

a first conductive layer, an active layer, and a second conductive layer each formed along at least a portion of the crystal surface, wherein the crystal surface plane comprises a plane having a plane orientation inclined at an angle ranging from about 5 to about 6 degrees with respect to at least one of a S-plane and a (11-22) plane.

Claim 84 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal layer comprising an approximately hexagonal pyramid, having a face oriented along an S-plane that diagonally intersects the substrate surface plane; and

a layer of a first conductivity type, an active layer, and a layer of a second conductivity type each formed along at least a portion of the approximately hexagonal pyramid, wherein a current is injected into the active layer such that a current density is lower near or at an apex of the approximately hexagonal pyramid than in the face of the approximately hexagonal pyramid.

Claim 85 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal grown layer formed by selective growth and including a crystal surface oriented along a crystal surface plane diagonally intersecting the substrate surface plane;

an active layer which is formed along at least a portion of the crystal grown layer that emits light upon injection of an amount of current;

and a reflecting region which is formed substantially parallel to the crystal surface plane and reflects at least a portion of the light emerging from the active layer, wherein the active layer is approximately parallel to a plane having a plane orientation inclined at an angle ranging from about 5 to about 6 degrees with respect to at least one of a S-plane and a (11-22) plane.

Claims 86-107 (canceled)